

TM10T3B-M,-H

TM10T3B-M,-H**MEDIUM POWER GENERAL USE
INSULATED TYPE****ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Voltage class		Unit
		M	H	
VRRM	Repetitive peak reverse voltage	400	800	V
VRSM	Non-repetitive peak reverse voltage	480	960	V
VR (DC)	DC reverse voltage	320	640	V
VDRM	Repetitive peak off-state voltage	400	800	V
VDSM	Non-repetitive peak off-state voltage	480	960	V
VD (DC)	DC off-state voltage	320	640	V

Symbol	Parameter	Conditions	Ratings	Unit
Io	DC output current	3-phase fullwave rectified, TC=79°C	20	A
ITSM, IFSM	Surge (non-repetitive) current	One half cycle at 60Hz, peak value	200	A
I ² t	I ² t for fusing	Value for one cycle of surge current	1.7 × 10 ²	A ² s
di/dt	Critical rate of rise of on-state current	VD=1/2VDRM, IG=0.5A, Tj=125°C	50	A/μs
PGM	Peak gate power dissipation		5.0	W
PG (AV)	Average gate power dissipation		0.5	W
VFGM	Peak gate forward voltage		10	V
VRGM	Peak gate reverse voltage		5.0	V
IFGM	Peak gate forward current		2.0	A
Tj	Junction temperature		−40~125	°C
Tstg	Storage temperature		−40~125	°C
Viso	Isolation voltage	Charged part to case	2500	V
—	Mounting torque	Mounting screw M4	0.98~1.47	N·m
			10~15	kg·cm
—	Weight	Typical value	130	g

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IRRM	Repetitive peak reverse current	Tj=125°C, VRRM applied	—	—	4.0	mA
IDRM	Repetitive peak off-state current	Tj=125°C, VDRM applied	—	—	4.0	mA
VTM, VFM	Forward voltage	Tj=125°C, ITM=IFM=20A, instantaneous meas.	—	—	1.3	V
dv/dt	Critical rate of rise of off-state voltage	Tj=125°C, VD=2/3VDRM	500	—	—	V/μs
VGT	Gate trigger voltage	Tj=25°C, VD=6V, RL=2Ω	—	—	2.0	V
VGD	Gate non-trigger voltage	Tj=125°C, VD=1/2VDRM	0.25	—	—	V
IGT	Gate trigger current	Tj=25°C, VD=6V, RL=2Ω	10	—	50	mA
Rth (j-c)	Thermal resistance	Junction to case (per 1/6 module)	—	—	4.5	°C/W
Rth (c-f)	Contact thermal resistance	Case to fin, Conductive grease applied (per 1/6 module)	—	—	0.6	°C/W
—	Insulation resistance	Measured with a 500V megohmmeter between main terminal and case	10	—	—	MΩ

Note: Items of the above table applies to the Thyristor part and the Diode part as circled in the following tables.

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Item	VRRM	VRSM	VR (DC)	VDRM	VDSM	VD (DC)	IT (RMS)	IT (AV)	ITSM	I^2t	di/dt
							IF (RMS)	IF (AV)	IFSM		
Thyristor	○	○	○	○	○	○	○	○	○	○	○
Diode	○	○	○	—	—	—	○	○	○	○	—

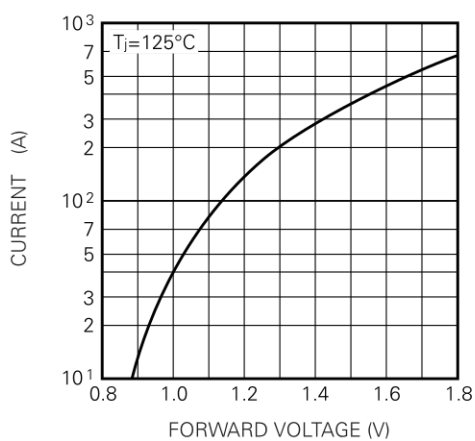
Item	PGM	PG (AV)	VFGM	IFGM	T _j	T _{stg}
Thyristor	○	○	○	○	○	○
Diode	—	—	—	—	○	○

ELECTRICAL CHARACTERISTICS

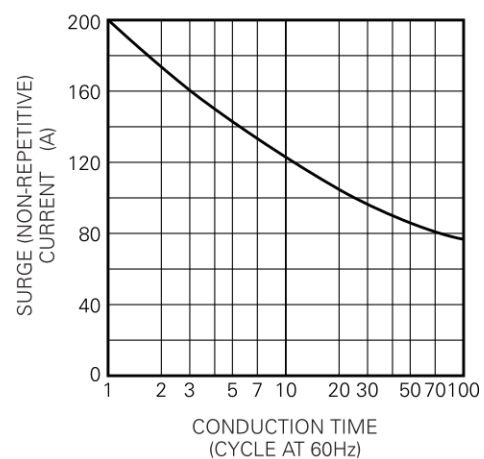
Item	IRR	IDRM	V _{TM}	dv/dt	VGT	VGD	IGT	R _{th} (j-c)	R _{th} (c-f)
			V _{FM}						
Thyristor	○	○	○	○	○	○	○	○	○
Diode	○	—	○	—	—	—	—	○	○

PERFORMANCE CURVES

MAXIMUM FORWARD CHARACTERISTIC



RATED SURGE (NON-REPETITIVE) CURRENT



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